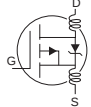


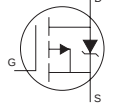
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IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.020	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.045	Ω	$V_{GS} = -10V, I_D = -2.8A$ ③
		—	—	0.070		$V_{GS} = -4.5V, I_D = -2.4A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	3.1	—	—	S	$V_{DS} = -15V, I_D = -2.8A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	—	59	nC	$I_D = -2.8A$
Q_{gs}	Gate-to-Source Charge	—	—	5.7		$V_{DS} = -2.4V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	21		$V_{GS} = -10V$, See Fig. 6 and 12 ③
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = -15V$ $I_D = -2.8A$ $R_G = 6.0\Omega$ $R_D = 5.3\Omega$, See Fig. 10 ③
t_r	Rise Time	—	33	—		
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		
t_f	Fall Time	—	47	—		
L_D	Internal Drain Inductance	—	2.5	—	nH	Between lead tip and center of die contact 
L_S	Internal Source Inductance	—	4.0	—		
C_{iss}	Input Capacitance	—	1100	—	pF	$V_{GS} = 0V$ $V_{DS} = -25V$ $f = 1.0\text{MHz}$, See Fig. 5
C_{oss}	Output Capacitance	—	490	—		
C_{rss}	Reverse Transfer Capacitance	—	220	—		

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-23		
V_{SD}	Diode Forward Voltage	—	—	-1.0	V	$T_J = 25^\circ\text{C}$, $I_S = -2.0A$, $V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	42	63	ns	$T_J = 25^\circ\text{C}$, $I_F = -2.8A$
Q_{rr}	Reverse Recovery Charge	—	64	96	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

② $I_{SD} \leq -2.8A$, $di/dt \leq 90A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

④ Surface mounted on FR-4 board, $t \leq 10\text{sec}$.

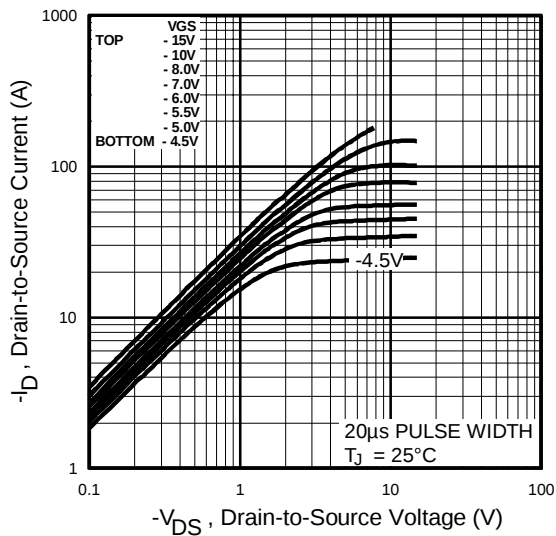


Fig 1. Typical Output Characteristics

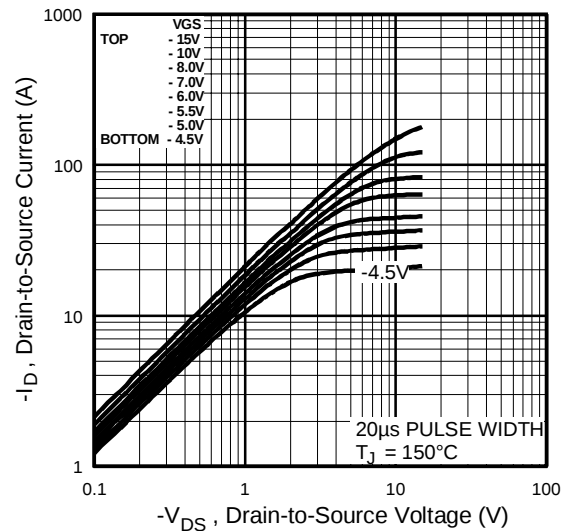


Fig 2. Typical Output Characteristics

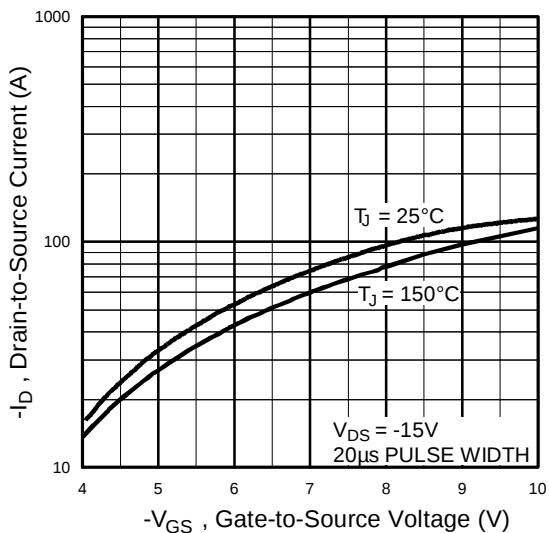


Fig 3. Typical Transfer Characteristics

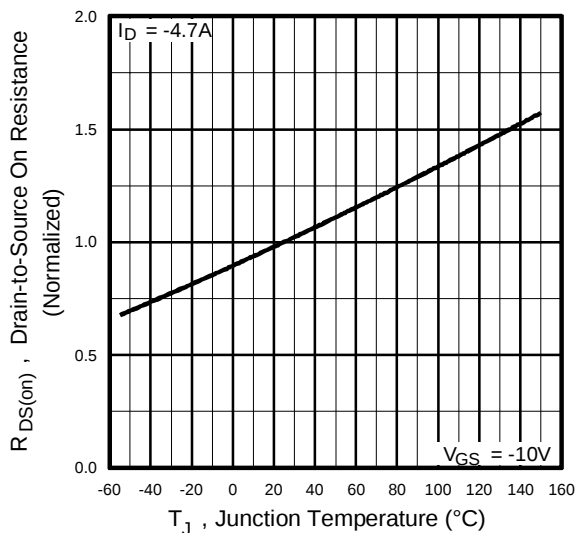
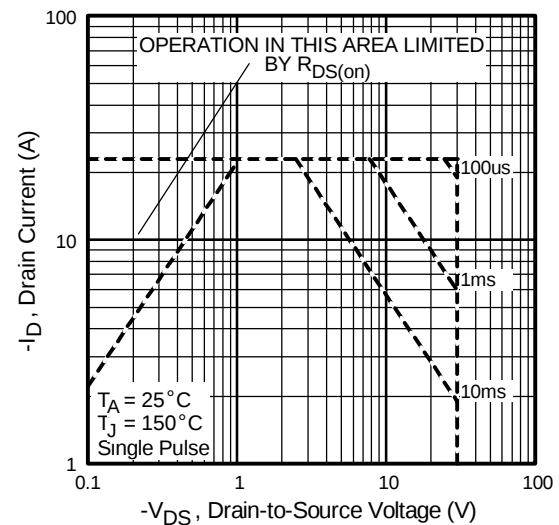
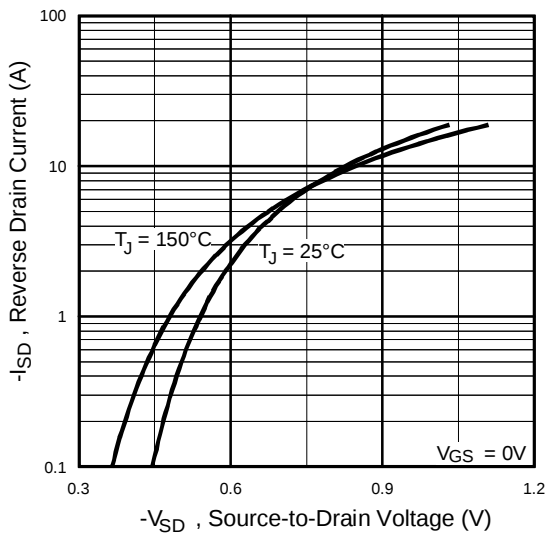
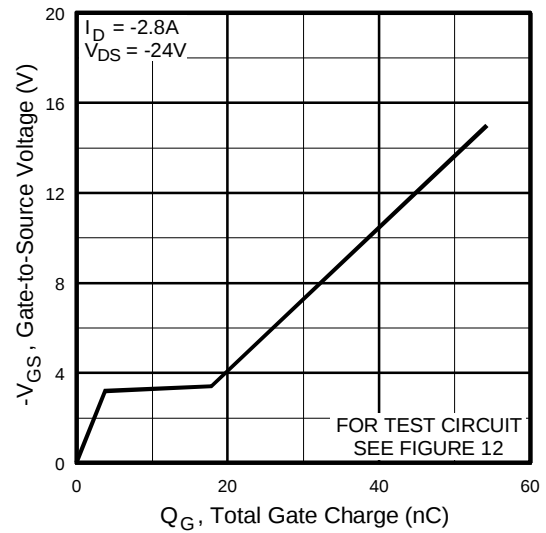
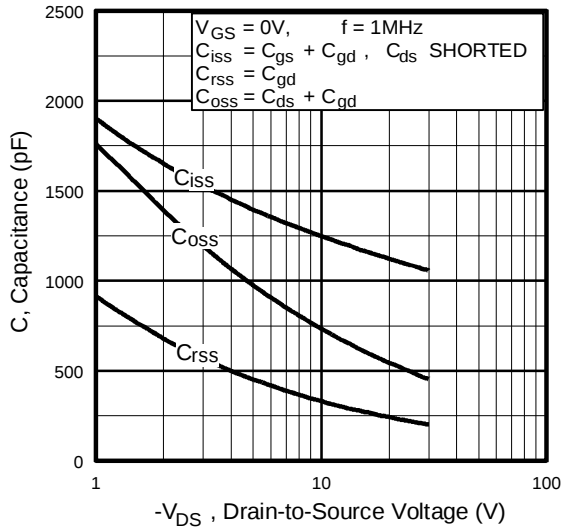


Fig 4. Normalized On-Resistance Vs. Temperature



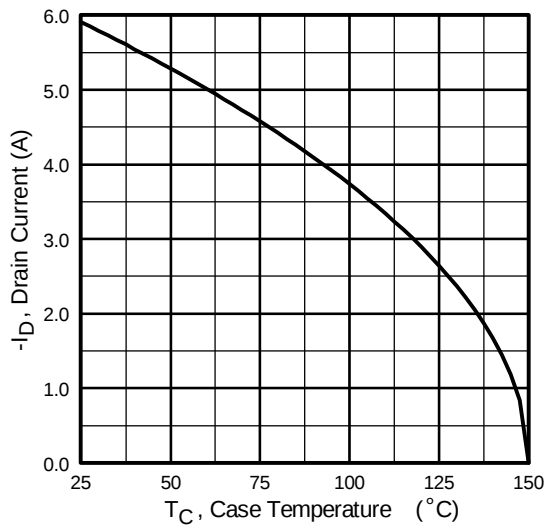


Fig 9. Maximum Drain Current Vs. Ambient Temperature

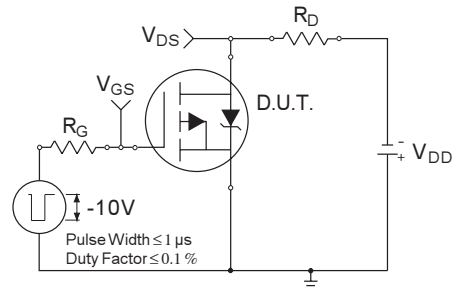


Fig 10a. Switching Time Test Circuit

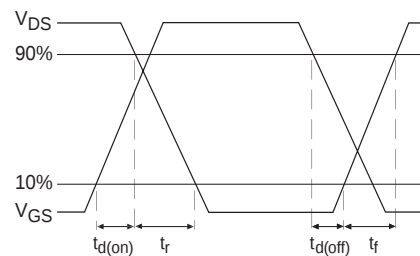
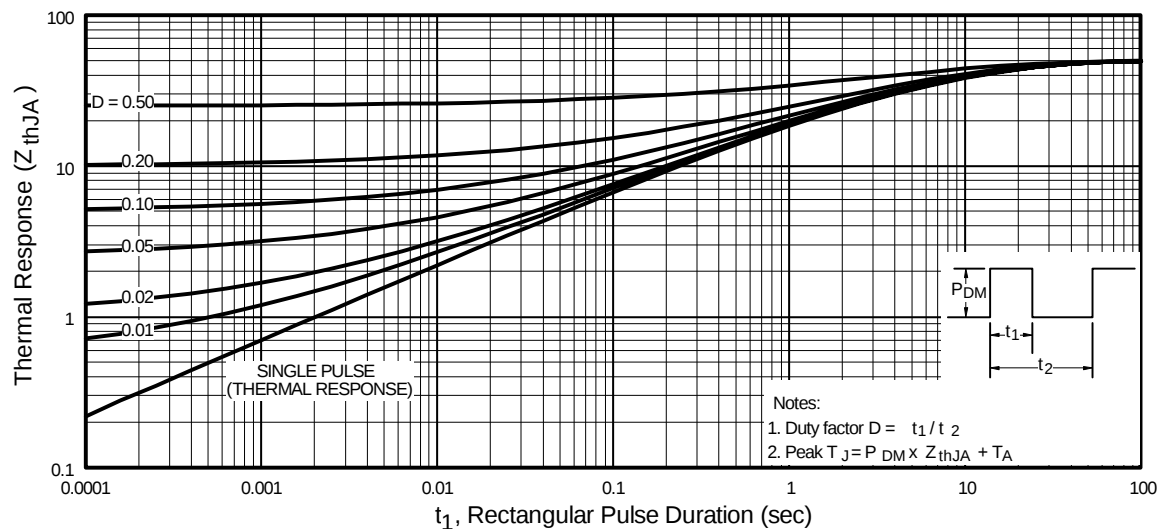


Fig 10b. Switching Time Waveforms



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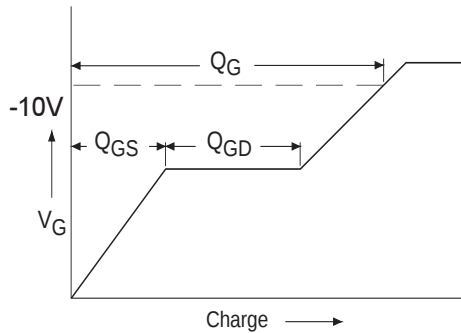


Fig 12a. Basic Gate Charge Waveform

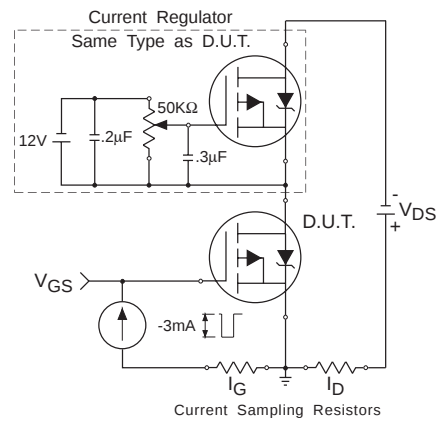
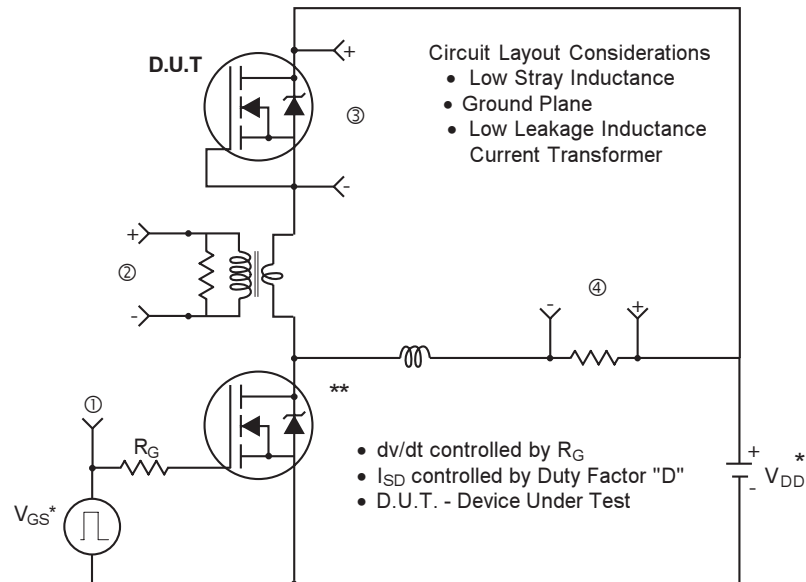


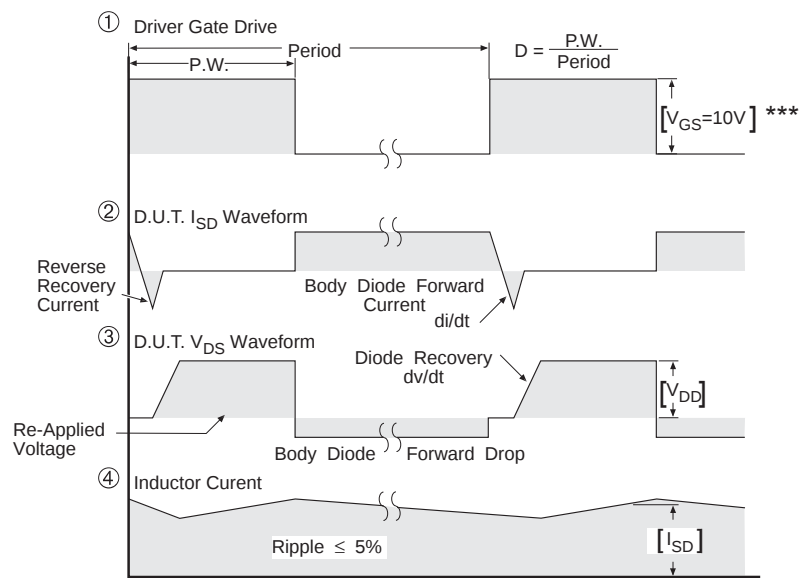
Fig 12b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements



*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 13. For P-Channel HEXFETS

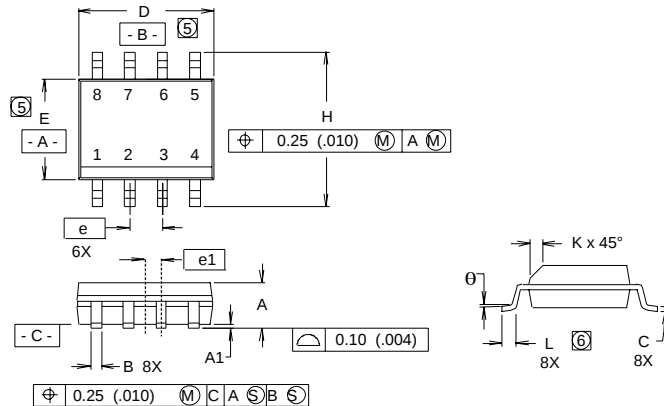
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Package Outline

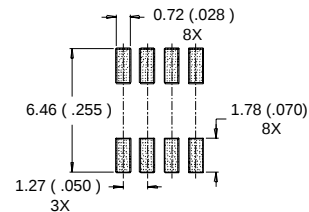
SO-8 Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
0	0°	8°	0°	8°

RECOMMENDED FOOTPRINT



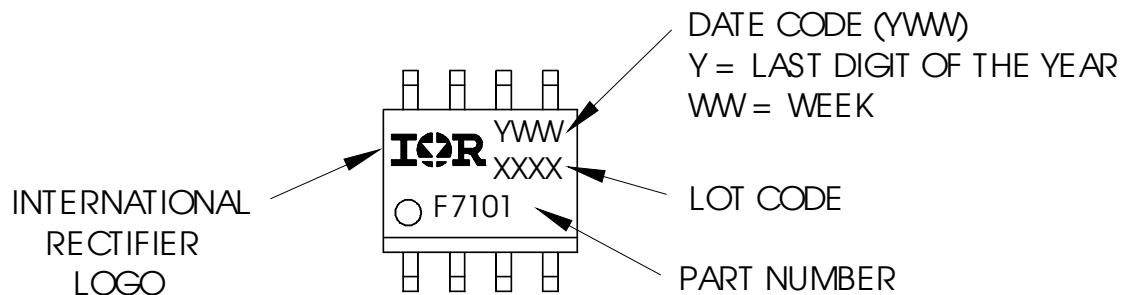
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

Part Marking Information

SO-8

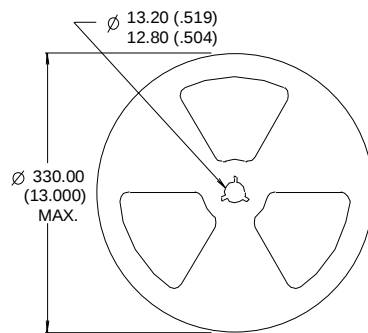
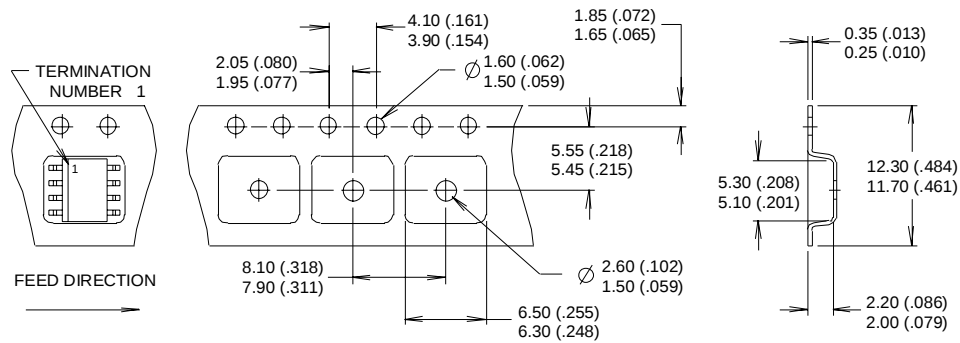
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Tape & Reel Information

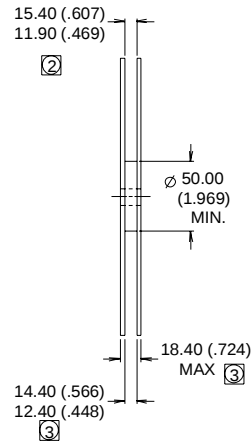
SO-8

Dimensions are shown in millimeters (inches)



NOTES:

- 1 CONFORMS TO EIA-481-1
- ② INCLUDES FLANGE DISTORTION @ OUTER EDGE
- ③ DIMENSIONS MEASURED @ HUB
- 4 CONTROLLING DIMENSION : METRIC



Data and specifications subject to change without notice.

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TAC Fax: (310) 252-7903

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